

L Number	Hits	S arch Text	DB	Time stamp
1	5583	(gat adj l ctr de) and ((titanium adj nitride) or TiN) and sili id	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:12
2	332	(gate adj electrode) and ((titanium adj nitride) or TiN) and silicide and ((fig or fig. or figure) near10 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:13
3	246	(gate adj electrode) and ((titanium adj nitride) or TiN) and silicide and ((fig or fig. or figure) near10 electrode) and (method or process).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:13
4	52	(gate adj electrode) and ((titanium adj nitride) or TiN) and silicide and ((fig or fig. or figure) near10 electrode) and (method or process).ti,ab,clm. and (barrier adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:14
5	12	(gate adj electrode) and ((titanium adj nitride) or TiN) and silicide and ((fig or fig. or figure) near10 electrode) and (method or process).ti,ab,clm. and (barrier adj layer) and (tin or (titanium near nitride)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:15
6	499	(gate adj electrode) and ((titanium adj nitride) or TiN) and silicide and (method or process).ti,ab,clm. and (barrier adj layer) and (tin or (titanium near nitride)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:15
7	183	(gate adj electrode).ti,ab,clm. and ((titanium adj nitride) or TiN) and silicide and (method or process).ti,ab,clm. and (barrier adj layer) and (tin or (titanium near nitride)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:16
8	111	(gate adj electrode).ti,ab,clm. and ((titanium adj nitride) or TiN) and silicide and (method or process).ti,ab,clm. and (barrier adj layer).ti,ab,clm. and (tin or (titanium near nitride)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:16
9	110	(gate adj electrode).ti,ab,clm. and ((titanium adj nitride) or TiN).ti,ab,clm. and silicide and (method or process).ti,ab,clm. and (barrier adj layer).ti,ab,clm. and (tin or (titanium near nitride)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:16
10	76	(gate adj lectrod ).ti,ab,clm. and ((titanium adj nitride) or TiN).ti,ab,clm. and silicide.ti,ab,clm. and (m thod or process).ti,ab,clm. and (barri r adj layer).ti,ab, lm. and (tin r (titanium near nitrid )).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:17

11	86	(gat adj lectr de).ti,ab,clm. and ((titanium adj nitrid ) or TiN).ti,ab,clm. and silicide.ti,ab,clm. and (meth d or pr c ss).ti,ab,clm. and (barri r near2 layer).ti,ab, lm. and (tin r (titanium n ar nitride)).ti,ab,clm.	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:17
12	19	(gate adj electrode).ti,ab,clm. and ((titanium adj nitride) or TiN).ti,ab,clm. and silicide.ti,ab,clm. and (method or process).ti,ab,clm. and (barrier near2 layer).ti,ab,clm. and (tin or (titanium near nitride)).ti,ab,clm. and (electrode same (film or layer) same barrier same ((titanium near nitride) or tin)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:20
13	0	09/9922804	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:20
14	1	09/922804	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:22
15	4374	(titanium near silicide) near5 (form or forming or formed)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:23
16	1255	electrode.clm. and (titanium near silicide) near5 (form or forming or formed)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:23
17	207	electrode.clm. and ((titanium near silicide) near5 (form or forming or formed)) and (titanium adj nitride).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:23
18	61	electrode.clm. and ((titanium near silicide) near5 (form or forming or formed)) and (titanium adj nitride).clm. and barrier.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:23
19	40	electrode.clm. and ((titanium near silicide) near5 (form or forming or formed)) and ((titanium adj nitride) near10 barrier).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:24

20	1	ele trod .clm. and ((titanium n ar silicid ) near5 no near5 (f rm r f rming r f rm d)) and ((titanium adj nitrid ) near10 barrier).clm.	USPAT; US-PGPUB; EPO; JP ; DERWENT; IBM_TDB	2004/06/02 15:24
21	40	electr de.clm. and ((titanium near silicide) near5 (form or forming or formed)) and ((titanium adj nitride) near10 barrier).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:25
22	0	(electrode.clm. and ((titanium near silicide) near5 (form or forming or formed)) and ((titanium adj nitride) near10 barrier).clm.) not silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:25
23	742	((titanium adj nitride) near5 barrier).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:25
24	85	((titanium adj nitride) near5 barrier).clm. and (gate adj electrode).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:25
25	32	((titanium adj nitride) near5 barrier).clm. and (gate adj electrode).clm.) not silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:26
26	1	((titanium adj nitride) near5 barrier).clm. and (gate adj electrode).clm.) not silicide and (electrode same (silicon or polysilicon) same (titanium adj nitride)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:28
27	160	(electrode same (silicon or polysilicon) same (titanium adj nitride)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:28
28	576	(electrode same (silicon or polysilicon) same (titanium adj nitride)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:28
29	323	((electrode same (silicon or polysilicon) same (titanium adj nitride)).ti,ab,clm.) not silicid	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:28

30	91	(((electrod same (silicon r p lysilicon) same (titanium adj nitride)).ti,ab, lm.) n t silicid ) and (ann al r ann aled r ann aling or tr at or treating r treated or tr atment or cure or cur d or uring)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:29
31	66	(((el ctrode sam ( ilic n r polysilic n) same (titanium adj nitride)).ti,ab,clm.) not silicide) and (anneal or annealed or annealing or treat or treating or treated or treatment or cure or cured or curing).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:29
33	20	(((electrode same (silicon or polysilicon) same (titanium adj nitride)).ti,ab,clm.) not silicide) and (anneal or annealed or annealing or treat or treating or treated or treatment or cure or cured or curing).ti,ab,clm. and temperature.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:33
34	10	(methodor or process) same electrode same (silicon or polysilicon or poly-silicon) same (barrier near5 (titanium adj nitride)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:54
35	643	(electrode near20 polysilicon near20 (barrier near2 layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:55
36	65	(electrode near20 polysilicon near20 (barrier near2 layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:55
37	11	(electrode near20 polysilicon near20 (barrier near2 layer)).clm. and ((barrier near2 layer) near20 (titanium near nitride)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 15:58
38	3	((electrode near20 polysilicon near20 (barrier near2 layer)).clm. and ((barrier near2 layer) near20 (titanium near nitride)).clm.) not silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 16:01
39	2	(((electrode near20 polysilicon near20 (barrier near2 layer)).clm. and ((barrier near2 layer) near20 (titanium near nitride)).clm.) not silicide) and (anneal or annealing or annealed)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 16:02

40	2	((lectrode near20 polysilic n near20 (barrier n ar2 lay r)).clm. and ((barrier n ar2 lay r) n ar20 (titanium near nitride)).clm.) n t silicide) and (anneal or ann aling or anneal d r treat or treating or tr ated or treatment)	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 16:02
41	2	((electrode near20 polysilicon near20 (barrier near2 layer)).clm. and ((barrier near2 layer) near20 (titanium near nitride)).clm.) not silicide) and (heat or heated or heating or anneal or annealing or annealed or treat or treating or treated or treatment)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/02 16:03